5. The semiconductor device according to claim 1, wherein the oxide semiconductor layer comprises at least indium (In) or zinc (Zn).

6. The semiconductor device according to claim 1, wherein the oxide semiconductor layer includes low-resistance regions between which the channel region is sandwiched.

7. The semiconductor device according to claim 1, wherein an end portion of the second buffer layer and an end portion of the first buffer layer are aligned.

8. A semiconductor device comprising:

an insulating layer;

a first buffer layer over the ~~first~~ insulating layer;

an oxide semiconductor layer over and in contact with the first buffer layer, the oxide semiconductor layer including a channel region;

a second buffer layer in contact with side surfaces of the oxide semiconductor layer, wherein the side surfaces of the oxide semiconductor layer are opposed to each other in a channel length direction,

wherein the second buffer layer is in direct contact with a top surface of the oxide semiconductor layer and side surfaces of the first buffer layer, wherein the side surfaces of the first buffer layer are opposed to each other in the channel length direction,

wherein each of the first buffer layer and the second buffer layer comprises an oxide of one or more elements selected from a group comprising aluminum, gallium, zirconium, hafnium, and a rare earth element,

wherein the second buffer layer is a single layer, and

wherein the second buffer layer is in direct contact with a top surface of the insulating layer.

9. The semiconductor device according to claim 8, wherein the oxide semiconductor layer has at least one region containing oxygen in excess of the stoichiometric ratio in a crystalline state.

10. The semiconductor device according to claim 8, wherein the oxide semiconductor layer is a crystalline semiconductor layer.

11. The semiconductor device according to claim 8,

wherein the oxide semiconductor layer comprises a crystal part,

wherein a c-axis of the crystal part is aligned in a direction parallel to a normal vector of a surface where the oxide semiconductor layer is formed or a normal vector of a surface of